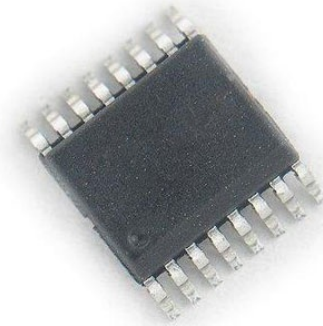


InGaP HBT 1 WATT POWER AMPLIFIER, 0.4

Manufacturers	Analog Devices, Inc
Package/Case	SSOP16
Product Type	Amplifier ICs
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for HMC452QS16G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

The HMC452QS16G(E) is a high dynamic range GaAs InGaP Heterojunction Bipolar Transistor (HBT) 1 watt MMIC power amplifier operating between 0.4 and 2.2 GHz. Packaged in a miniature 16 lead QSOP plastic package, the amplifier gain is typically 22.5 dB at 0.4 GHz and 9 dB at 2.1 GHz. Utilizing a minimum number of external components and a single +5V supply, the amplifier output IP3 can be optimized to +43 dBm at 0.4 GHz or +48 dBm at 2.1 GHz. The power control (VPD) can be used for full power down or RF output power/current control. The high output IP3 and PAE make the HMC452QS16G(E) ideal power amplifier for Cellular/ PCS/3G, WLL, ISM and Fixed Wireless applications.

Features

- Output IP3: +48 dBm
- 22.5 dB Gain @ 400 MHz
- 9 dB Gain @ 2100 MHz
- 53% PAE @ +31 dBm Pout
- Single +5V Supply
- Integrated Power Control (VPD)
- QSOP16G SMT Package: 29.4 mm²

Application

- GSM, GPRS & EDGE
- CDMA & W-CDMA
- CATV/Cable Modem
- Fixed Wireless & WLL

Related Products



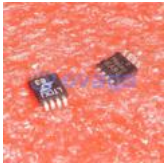
[HMC591LP5E](#)

Analog Devices, Inc
QFN32



[HMC589AST89E](#)

Analog Devices, Inc
SOT-89



[LTC6102HMS8#PBF](#)

Analog Devices, Inc
8MSOP



[HMC464LP5](#)

Analog Devices, Inc
QFN32



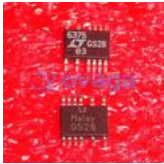
[HMC902LP3E](#)

Analog Devices, Inc
QFN-16



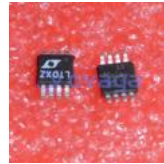
[LTC6102HMS8](#)

Analog Devices, Inc
MSOP8



[LT6375HMS#PBF](#)

Analog Devices, Inc
16MSOP



[LTC6102HMS8-1#PBF](#)

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8-MSOP